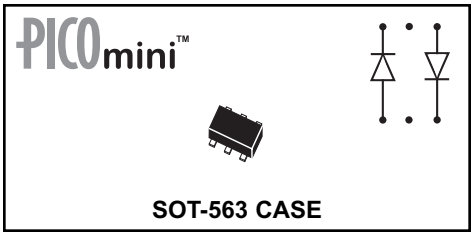
CMLD6001DO

SURFACE MOUNT
PICOmini™
DUAL, ISOLATED, OPPOSING
LOW LEAKAGE SILICON
SWITCHING DIODES



SOT-563 CASE

Central™
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMLD6001DO type contains Two (2) Isolated Opposing Configuration, Silicon Switching Diodes, manufactured by the epitaxial planar process, epoxy molded in a PICOmini™ surface mount package. These devices are designed for switching applications requiring extremely low leakage.

Marking code: C60

MAXIMUM RATINGS: (T_A=25°C)	**SYMBOL**		**UNITS**
Continuous Reverse Voltage	V_R	75	V
Peak Repetitive Reverse Voltage	V_{RRM}	100	V
Continuous Forward Current	I_F	250	mA
Forward Surge Current, tp=1μs	I_{FSM}	4000	mA
Forward Surge Current, tp=1s	I_{FSM}	1000	mA
Power Dissipation	P_D	250	mW
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	°C
Thermal Resistance	Θ_{JA}	500	°C/W

ELECTRICAL CHARACTERISTICS PER DIODE: (T_A=25°C unless otherwise noted)

SYMBOL	**TEST CONDITIONS**	**MIN**	**MAX**	**UNITS**
I_R	V_R=75V		500	pA
BV_R	I_R=100μA	100		V
V_F	I_F=1.0mA		0.85	V
V_F	I_F=10mA		0.95	V
V_F	I_F=100mA		1.1	V
C_T	V_R=0, f=1 MHz		2.0	pF
t_{rr}	I_R=I_F=10mA, R_L=100Ω Rec. to 1.0mA		3.0	μs

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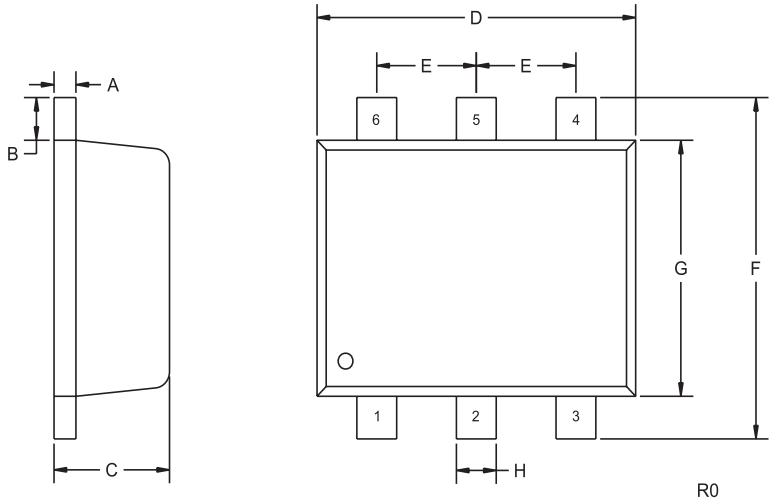
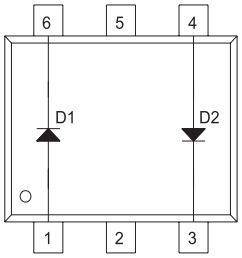
SOT-563 CASE - MECHANICAL OUTLINE



DIMENSIONS				
	INCHES		MILLIMETERS	
SYMBOL	MIN	MAX	MIN	MAX
A	0.004	0.007	0.10	0.18
B	0.008		0.20	
C	0.022	0.024	0.56	0.60
D	0.059	0.067	1.50	1.70
E	0.020		0.50	
F	0.061	0.067	1.55	1.70
G	0.047		1.20	
H	0.006	0.012	0.15	0.30

SOT-563 (REV: R0)

PIN CONFIGURATION



LEAD CODE:
1) ANODE D1
2) NC
3) CATHODE D2
4) ANODE D2
5) NC
6) CATHODE D1

MARKING CODE: C60

R1 (6-June 2008)